

## **KSD882**

# **Audio Frequency Power Amplifier Low Speed Switching** WWW.DZSC.COM

Complement to KSB772



## **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

| Symbol           | Parameter                                    | Value      | Units |  |
|------------------|--|------------|-------|--|
| V <sub>CBO</sub> | Collector- Base Voltage                      | 40         | V     |  |
| V <sub>CEO</sub> | Collector-Emitter Voltage                    | 30         | V     |  |
| V <sub>EBO</sub> | Emitter- Base Voltage                        | 5          | V     |  |
| I <sub>C</sub>   | Collector Current (DC)                       | 3          | А     |  |
| I <sub>CP</sub>  | *Collector Current (Pulse)                   | 7          | А     |  |
| I <sub>B</sub>   | Base Current                                 | 0.6        | Α     |  |
| P <sub>C</sub>   | Collector Dissipation (T <sub>C</sub> =25°C) | 10         | W     |  |
| P <sub>C</sub>   | Collector Dissipation (T <sub>a</sub> =25°C) | 1W.V       | W     |  |
| T <sub>J</sub>   | Junction Temperature                         | 150        | °C    |  |
| T <sub>STG</sub> | Storage Temperature                          | - 55 ~ 150 | °C    |  |

<sup>\*</sup> PW≤10ms, Duty Cycle≤50%

## Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

| Symbol                               | Parameter                             | Test Condition   | Min.     | Тур.       | Max. | Units |
|--------------------------------------|---------------------------------------|--|----------|------------|------|-------|
| I <sub>CBO</sub>                     | Collector Cut-off Current             | $V_{CB} = 30V, I_{E} = 0$                                |          |            | 1    | μΑ    |
| I <sub>EBO</sub>                     | Emitter Cut-off Current               | $V_{EB} = 3V, I_{C} = 0$                                 |          |            | 1    | μΑ    |
| h <sub>FE1</sub><br>h <sub>FE2</sub> | *DC Current Gain                      | $V_{CE} = 2V, I_{C} = 20mA$<br>$V_{CE} = 2V, I_{C} = 1A$ | 30<br>60 | 150<br>160 | 400  | 7DP   |
| V <sub>CE</sub> (sat)                | *Collector-Emitter Saturation Voltage | $I_C = 2A, I_B = 0.2A$                                   |          | 0.3        | 0.5  | V     |
| V <sub>BE</sub> (sat)                | *Base-Emitter Saturation Voltage      | $I_C = 2A, I_B = 0.2A$                                   |          | 1.0        | 2.0  | V     |
| f <sub>T</sub>                       | Current Gain Bandwidth Product        | $V_{CE} = 5V, I_{E} = 0.1A$                              |          | 90         |      | MHz   |
| C <sub>ob</sub>                      | Output Capacitance                    | $V_{CB} = 10V$ , $I_E = 0$<br>f = 1MHz                   |          | 45         |      | pF    |

<sup>\*</sup> Pulse Test: PW≤350μs, Duty Cycle≤2% Pulsed

# h<sub>FE</sub> Classification

| Classification   | R        | 0         | Υ         | G         |
|------------------|----------|-----------|-----------|-----------|
| h <sub>FE2</sub> | 60 ~ 120 | 100 ~ 200 | 160 ~ 320 | 200 ~ 400 |

## **Typical Characteristics**

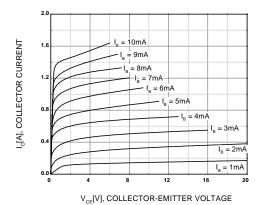


Figure 1. Static Characteristic

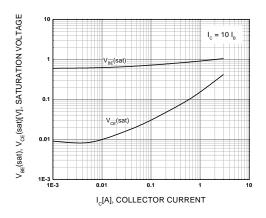


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

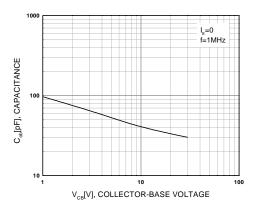


Figure 5. Collector Output Capacitance

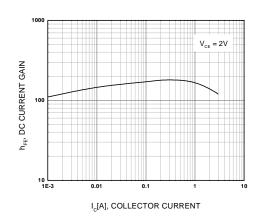


Figure 2. DC current Gain

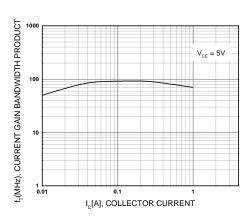


Figure 4. Current Gain Bandwidth Product

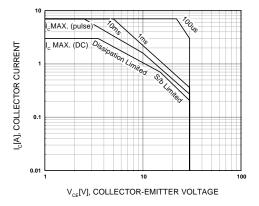
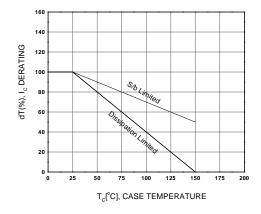
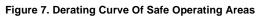


Figure 6. Safe Operating Area

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# **Typical Characteristics** (Continued)





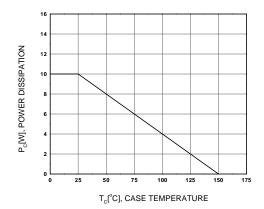
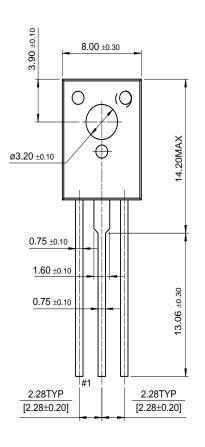


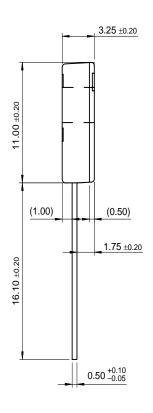
Figure 8. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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